

wherein the barrier metal is formed by using CVD of at least one of tungsten nitride  $WN_x$ , where x is an atomic fraction of N and comprises a range from 0.5 to 1.0, and tungsten silicide nitride  $WSi_yN_z$ , where y is an atomic fraction of Si and comprises a range from 0.01 to 0.2, and z is an atomic fraction of N and comprises a range from 0.02 to 0.2.

62. (Amended) An electrode of a circuit element formed on a semiconductor substrate, comprising:

B1  
a polysilicon layer;

a barrier metal formed on the polysilicon layer; and

a metal layer formed on the barrier metal,

wherein the barrier metal comprises at least one of:

a tungsten nitride layer, and

a tungsten silicide nitride layer,

and the barrier metal is formed of at least one of tungsten nitride  $WN_x$ , where x is an atomic fraction of N and comprises a range from 0.5 to 1.0, and tungsten silicide nitride  $WSi_yN_z$ , where y is an atomic fraction of Si and comprises a range from 0.01 to 0.2, and z is an atomic fraction of N and comprises a range from 0.02 to 0.2.

#### REMARKS

Favorable reconsideration of this application, as presently amended and in light of the following discussion, is respectfully requested.

Claims 28-62 are presently active in this application. Claims 39, 40, and 62 having been amended by way of the present amendment.